/ Descriptions

VRW056 ṂṂ Ḅ QSQ ÆṀ ч s ‖ ㄱ Silicon NPN transistor in a SOT-23 Plastic Package.

/ Features

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High I_C, high h_{FE}.

/ Applications

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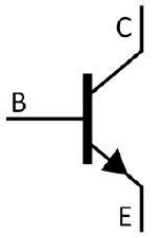
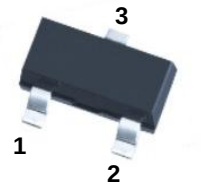
Use in audio output driver stage amplifier applications.

/ Equivalent Circuit



/ Pinning



PIN1 χ Base PIN 2 χ Emitter PIN 3 χ Collector

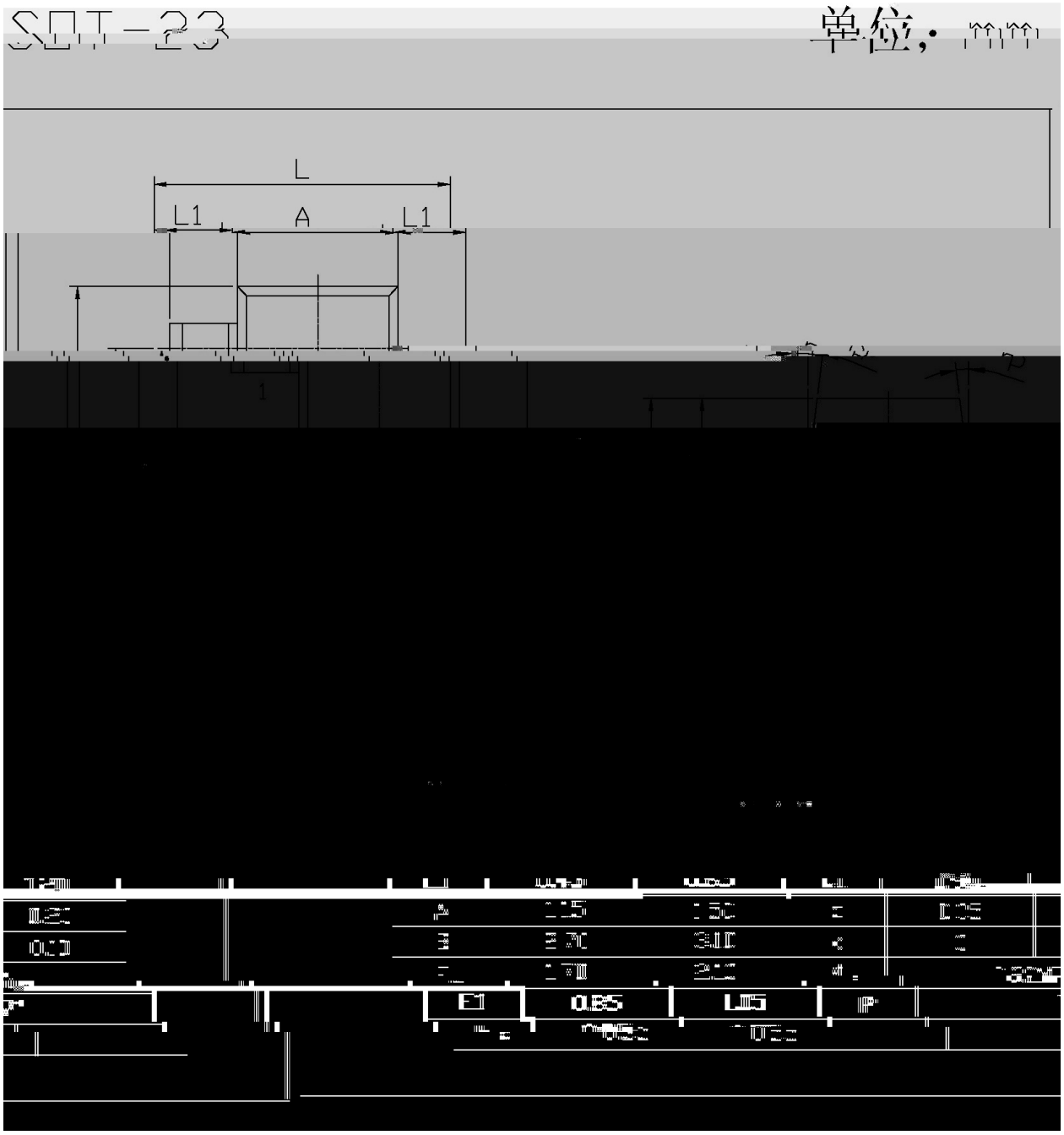
/ h_{FE} Classifications & Marking

h_{FE} Classifications Symbol	B	C	D
h_{FE} Range	300~550	500~700	650~1000
Marking	H28B	H28C	H28D

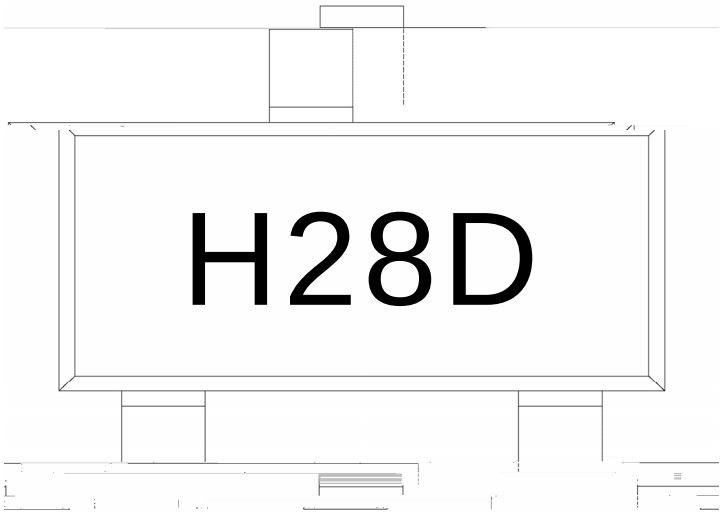
v ˝Ω Parameter	٩ N Symbol	˝Ω Ö Rating	D Ч Unit
Collector to Base Voltage	V_{CBO}	40	V
Collector to Emitter Voltage	V_{CEO}	20	V
Emitter to Base Voltage	V_{EBO}	6.0	V
Collector Current - Continuous	I_C	1.0	A
Collector Power Dissipation	P_C	400	mW
Junction Temperature	T_j	150	ł
Storage Temperature Range	T_{stg}	-55 Ќ 150	ł

v ˝Ω Parameter	٩ N Symbol	Ш :† ţ Test Conditions	ώ ņ Ö Min	Ɛ ʒ Ö Typ	ώ ² Ö Max	D Ч Unit
Collector to Base Breakdown Voltage	V_{CBO}	I_C=0.1mA I_E=0	40			V
Collector to Emitter Breakdown Voltage	V_{CEO}	I_C=1.0mA I_B=0	20			V
Emitter to Base Breakdown Voltage	V_{EBO}	I_E=0.1mA I_C=0	6.0			V
Collector Cut-Off Current	I_{CBO}	V_{CB}=40 V I_E=0			1.0	A
Emitter Cut-Off Current	I_{CEO}	V_{CE}=20V I_B=0			5.0	A
Emitter Base Cut-Off Current	I_{EBO}	V_{EB}=5.0V I_C=0			0.1	A
DC Current Gain	$h_{FE(1)}$	V_{CE}=1.0V I_C=100mA	300		1000	
	$h_{FE(2)}$	V_{CE}=1.0V I_C=500mA	300			
	$h_{FE(3)}$	V_{CE}=1.0V I_C=300mA	300			
	$h_{FE(4)}$	V_{CE}=1.0V I_C=1.0mA	290			

/ Package Dimensions



/ Marking Instructions



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H χ ѭ ϛ и Ґϧ

28 χ ѭ ϛ N Ґϧ

D χ ѭ h_{FE} ‘ 6 Ґϧ

Note:

H: Company Code.

28: Product Type.

D: h_{FE} Classifications Symbol.